Solid State Power Amplifier
20 to 2500MHz
MODEL BHED27258-200

Features:
- GaN Technology for Ultra Wideband Operation
  - 20 – 1000MHz, 125W
  - 1000 – 2500MHz, 200W
- Integrated T/R Switch for Each Band
- Compact Configuration
- Simultaneous Operation of Both Bands

Performance Specifications

- Frequency Range: 20 to 2500MHz in two bands
- RF Power Out (after T/R Switches):
  - Band 1 (20-1000MHz) 125 Watts Typical
  - Band 2 (1000-2500MHz) 200 Watts Typical
- RF Input: 0 dBm; +3dB Typical
- RF Input Overdrive: 8 dBm Max.
- Class of Operation: AB Linear
- Modulation Format: Multi-tone, CW, AM, FM, SSB, Pulse
- VSWR: 2.0:1 with 0.5dB turndown
- Harmonic Rejection: <-13 dBC Typical
- Spurious: <-60 dBC
- AM Distortion (85% DOM): 10% max
- T/R Isolation: 50dB
- T/R Switching Speed: 50µsec
- Noise Power Output: Transmit Mode: -86dBm/Hz typical
  Receive Mode (NQ ON): -150dBm/Hz
- Noise Quieting Speed: 10µsec
- Digital Display: Forward Power, Reflected Power, Fault Status, VSWR, Thermal Fault, PA Status, PS Status
- Control Interface: RS-422, Ethernet
- Local Indicators: Thermal Fault, T/R Status, Power On
- Internal Protection: Load VSWR; Overdrive: Over-Current; Hot Switch; Thermal Overload
- Primary Power: 110/220VAC; 50/60Hz
- Power Consumption: 1850W
- RF Connectors:
  - RF Input and receive Ports: N Type female
  - RF Output: N Type female
- Environmental:
  - Operating Temperature: -10° to +55°C
  - Operating Altitude: 10,000 feet
  - Shock/Vibration: MIL-STD-810G
  - Size: 5U high (8.75”)
  - Weight: 60 lbs.

Comtech PST (CPST) is pleased to introduce Model BHED27258-200, a compact, efficient dual band 20-2500MHz solid state high power amplifier. This highly integrated design utilizes the latest GaN technology, which achieves one of the highest power density-to-footprint ratios of amplifier building blocks throughout the industry.